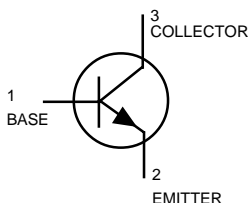
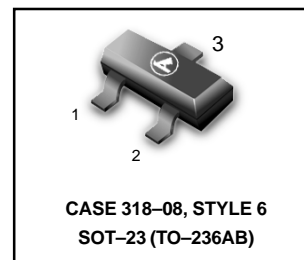


# General Purpose Transistors

## NPN Silicon



**BCX70GLT1**  
**BCX70JLT1**  
**BCX70KLT1**



### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CE0}$	45	Vdc
Collector–Base Voltage	$V_{CBO}$	45	Vdc
Emitter–Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current — Continuous	$I_C$	200	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR– 5 Board, (1) $T_A = 25^\circ\text{C}$	$P_D$	225	mW
Derate above $25^\circ\text{C}$		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	$P_D$	300	mW
Derate above $25^\circ\text{C}$		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

### DEVICE MARKING

BCX70GLT1 = AG ; BCX70JLT1 = AJ ; BCX70KLT1 = AK ;

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ( $I_C = 2.0\text{mAdc}, I_E = 0$ )	$V_{(BR)CEO}$	45	—	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 1.0\ \mu\text{Adc}, I_C = 0$ )	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ( $V_{CE} = 32\ \text{Vdc},$ )	$I_{CES}$	—	20	nAdc
( $V_{CE} = 32\ \text{Vdc}, T_A = 150^\circ\text{C}$ )		—	20	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 4.0\ \text{Vdc}, I_C = 0$ )	$I_{EBO}$	—	20	nAdc

1. FR– 5 =  $1.0 \times 0.75 \times 0.062$  in.

2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

**BCX70GLT1 BCX70JLT1 BCX70KLT1**

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = 10 \mu\text{Adc}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	$h_{FE}$	—	—	—
	BCX70G	—	—	
	BCX70J	40	—	
	BCX70K	100	—	
( $I_C = 2.0 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	BCX70G	120	220	
	BCX70J	250	460	
	BCX70K	380	630	
( $I_C = 50 \text{ mAdc}$ , $V_{CE} = 1.0 \text{ Vdc}$ )	BCX70G	60	—	
	BCX70J	90	—	
	BCX70K	100	—	
Collector–Emitter Saturation Voltage ( $I_C = 50 \text{ mAdc}$ , $I_B = 1.25 \text{ mAdc}$ ) ( $I_C = 10 \text{ mAdc}$ , $I_B = 0.25 \text{ mAdc}$ )	$V_{CE(sat)}$	—	0.55 0.35	Vdc
Base–Emitter Saturation Voltage ( $I_C = 50 \text{ mAdc}$ , $I_B = 1.25 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 0.25 \text{ mAdc}$ )	$V_{BE(sat)}$	0.7 0.6	1.05 0.85	Vdc
Base–Emitter On Voltage ( $I_C = 2.0 \text{ mAdc}$ , $V_{CE} = 0.5 \text{ Vdc}$ )	$V_{BE(on)}$	0.55	0.75	Vdc

**SMALL–SIGNAL CHARACTERISTICS**

Current–Gain — Bandwidth Product ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ , $f = 100 \text{ MHz}$ )	$f_T$	125	—	MHz
Output Capacitance ( $V_{CB} = 10 \text{ Vdc}$ , $I_C = 0$ , $f = 1.0 \text{ MHz}$ )	$C_{obo}$	—	4.5	pF
Small–Signal Current Gain ( $I_C = 2.0 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	$h_{FE}$	—	—	—
	BCX70G	125	250	
	BCX70J	250	500	
	BCX70K	350	700	
Noise Figure ( $V_{CE} = 5.0 \text{ Vdc}$ , $I_C = 0.2 \text{ mAdc}$ , $R_S = 2.0 \text{ k}\Omega$ , $f = 1.0 \text{ kHz}$ , $BW = 200 \text{ Hz}$ )	NF	—	6.0	dB

**SWITCHING CHARACTERISTICS**

Turn–On Time ( $I_C = 10 \text{ mAdc}$ ; $I_{B1} = 1.0 \text{ mAdc}$ )	$t_{on}$	—	150	ns
Turn–Off Time ( $I_{B2} = 1.0 \text{ mAdc}$ ; $V_{BB} = 3.6 \text{ Vdc}$ ; $R_1 = R_2 = 5.0 \text{ k}\Omega$ ; $R_L = 990 \Omega$ )	$t_{off}$	—	800	ns

**EQUIVALENT SWITCHING TIME TEST CIRCUITS**

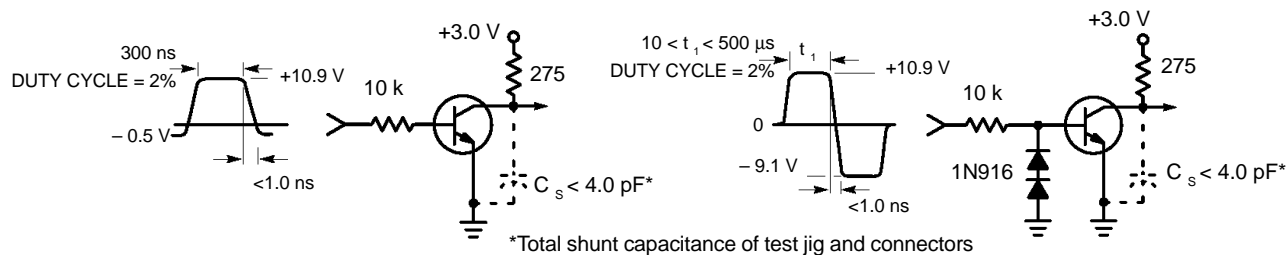


Figure 1. Turn–On Time

Figure 2. Turn–Off Time

BCX70GLT1 BCX70JLT1 BCX70KLT1

TYPICAL NOISE CHARACTERISTICS

( $V_{CE} = 5.0 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ )

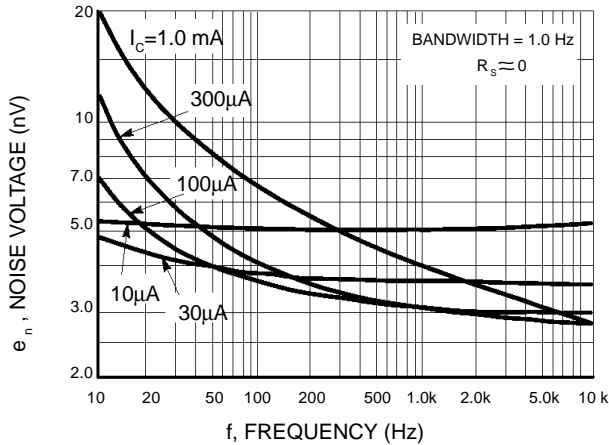


Figure 3. Noise Voltage

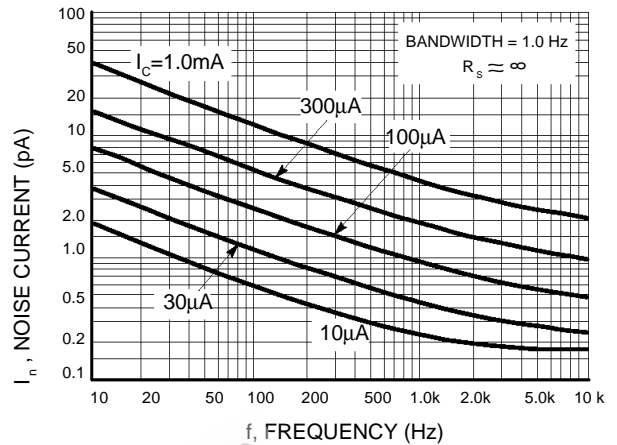


Figure 4. Noise Current

NOISE FIGURE CONTOURS

( $V_{CE} = 5.0 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ )

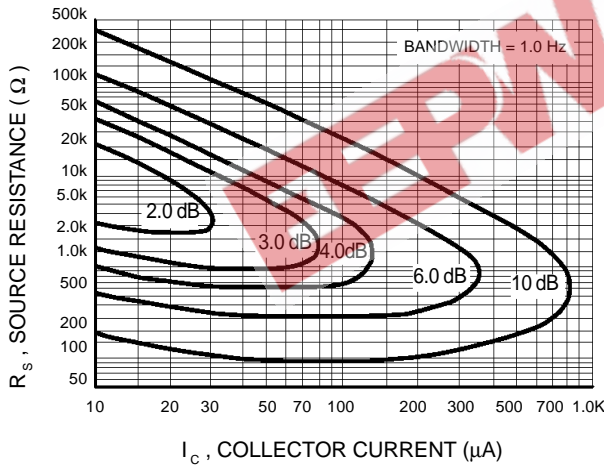


Figure 5. Narrow Band, 100 Hz

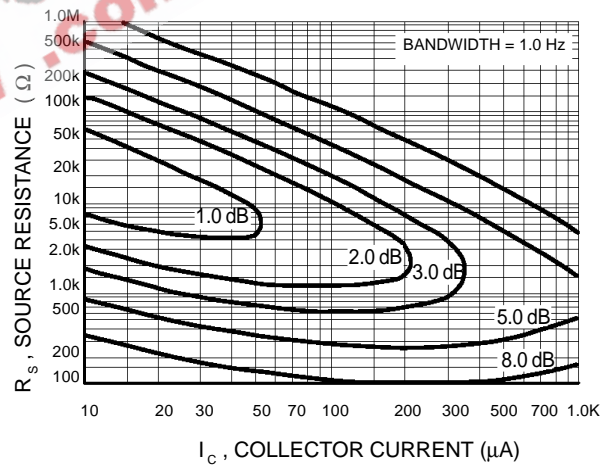


Figure 6. Narrow Band, 1.0 kHz

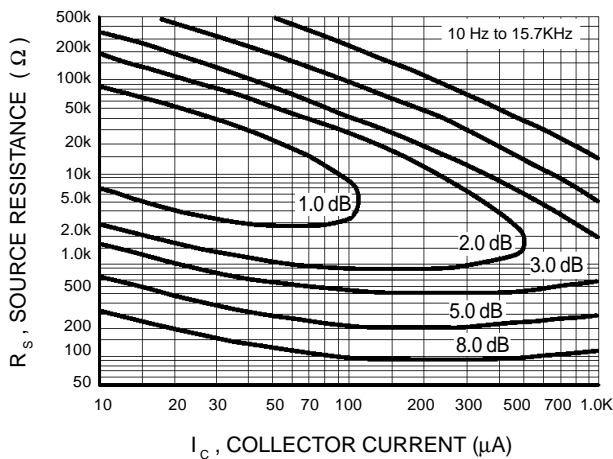


Figure 7. Wideband

Noise Figure is Defined as:

$$NF = 20 \log_{10} \left( \frac{e_n^2 + 4KTR_s + I_n^2 R_s^2}{4KTR_s} \right)^{1/2}$$

- $e_n$  = Noise Voltage of the Transistor referred to the input. (Figure 3)
- $I_n$  = Noise Current of the Transistor referred to the input. (Figure 4)
- $K$  = Boltzman's Constant ( $1.38 \times 10^{-23} \text{ J}^\circ\text{K}$ )
- $T$  = Temperature of the Source Resistance ( $^\circ\text{K}$ )
- $R_s$  = Source Resistance ( $\Omega$ )

BCX70GLT1 BCX70JLT1 BCX70KLT1

TYPICAL STATIC CHARACTERISTICS

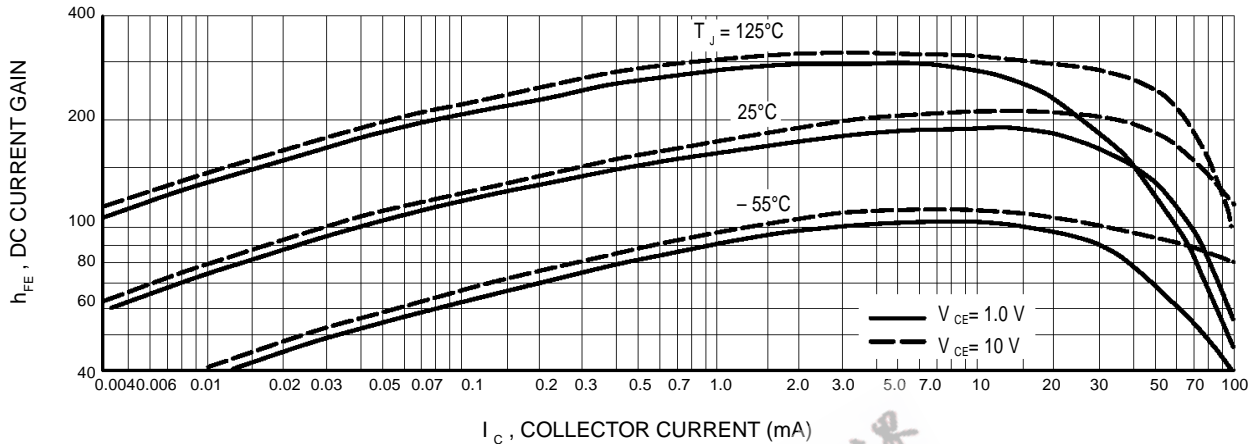


Figure 8. DC Current Gain

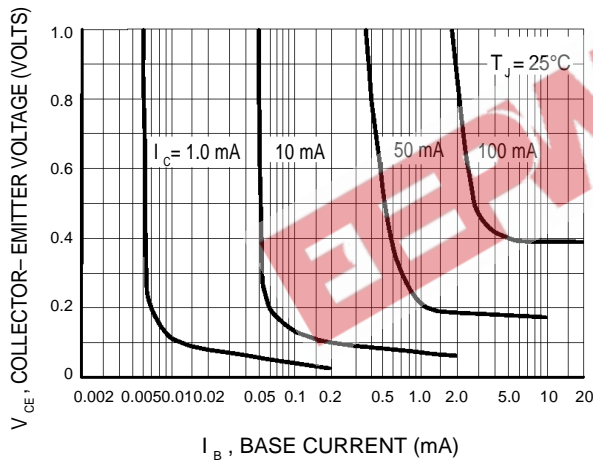


Figure 9. Collector Saturation Region

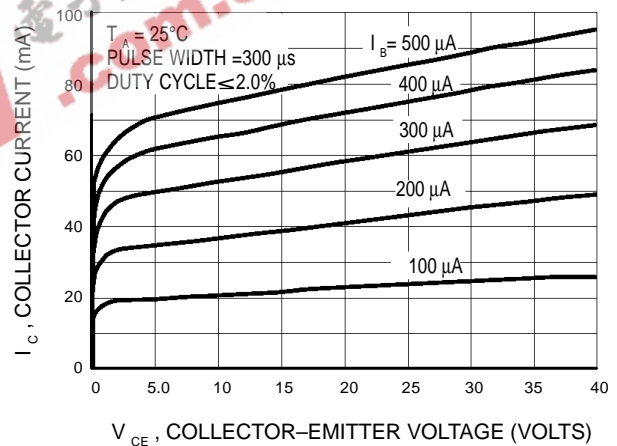


Figure 10. Collector Characteristics

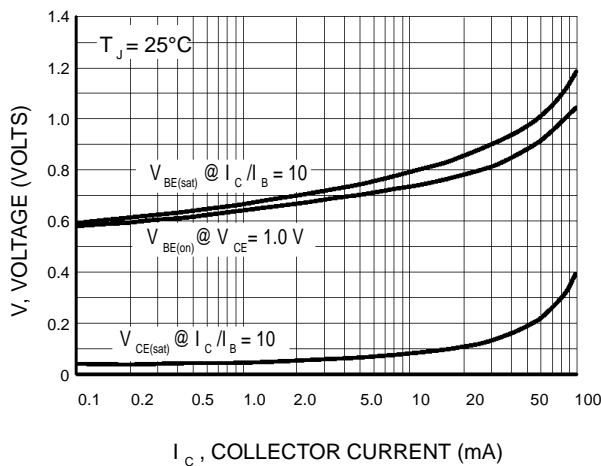


Figure 11. "On" Voltages

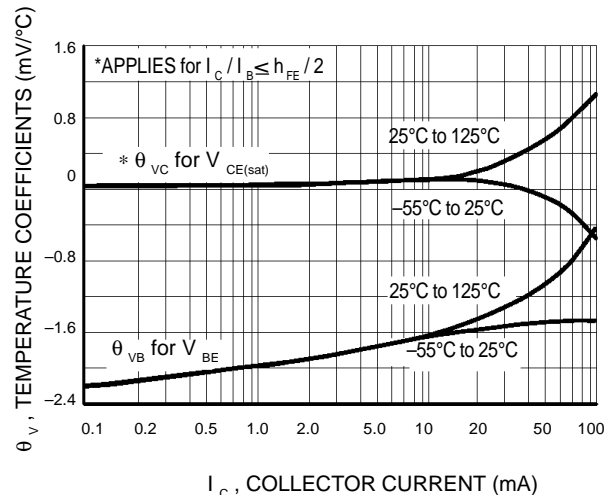


Figure 12. Temperature Coefficients

BCX70GLT1 BCX70JLT1 BCX70KLT1

TYPICAL DYNAMIC CHARACTERISTICS

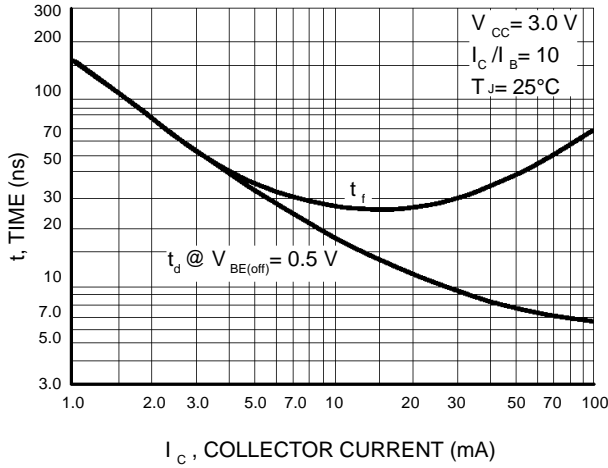


Figure 13. Turn-On Time

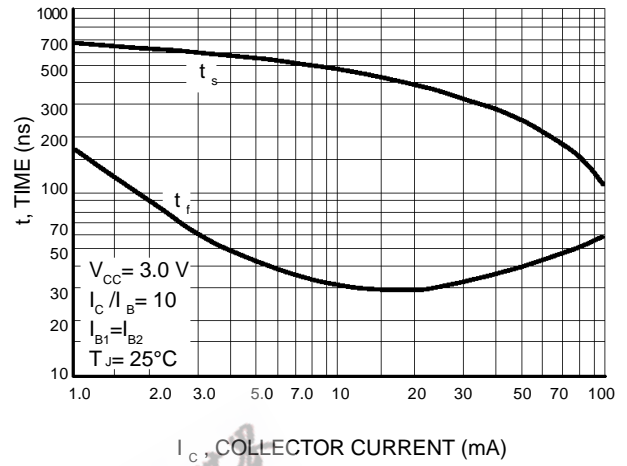


Figure 14. Turn-Off Time

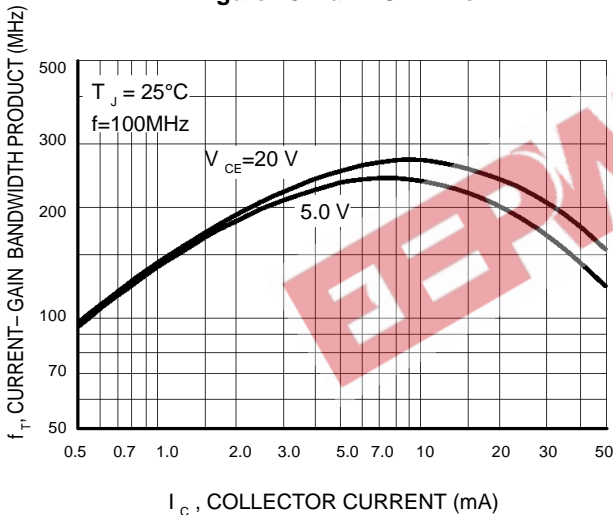


Figure 15. Current-Gain — Bandwidth Product

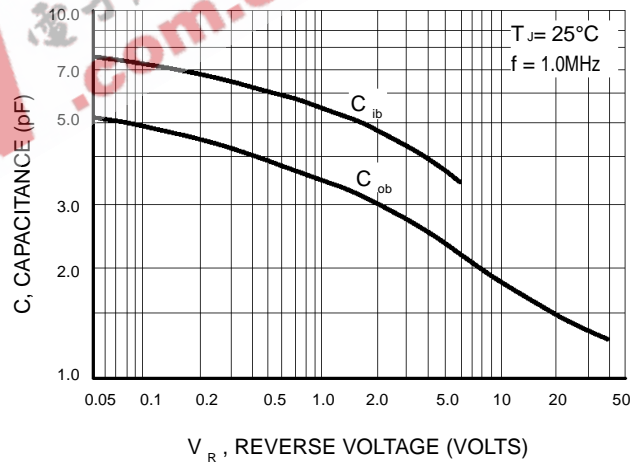


Figure 16. Capacitance

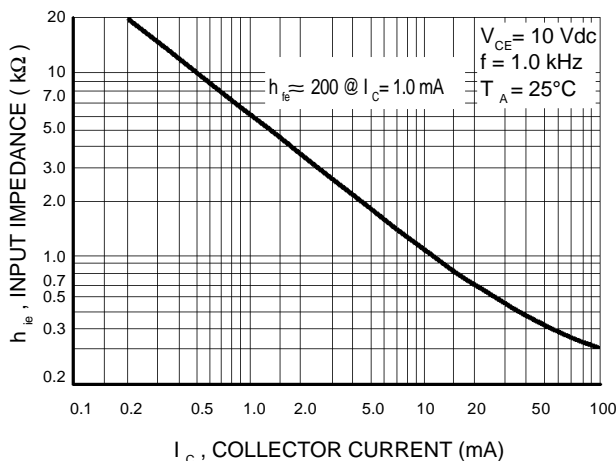


Figure 17. Input Impedance

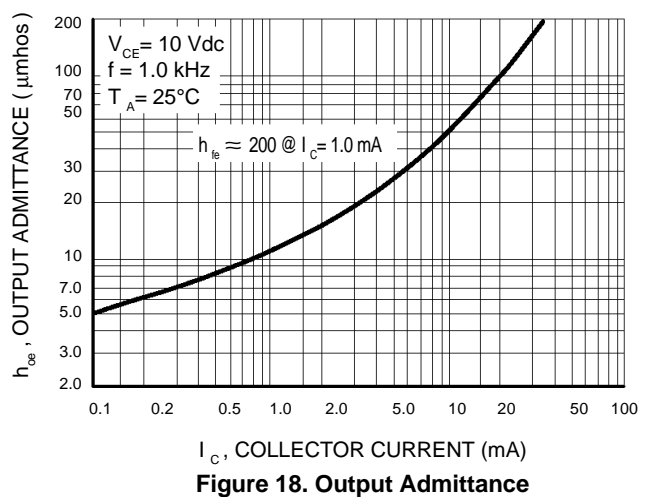


Figure 18. Output Admittance

BCX70GLT1 BCX70JLT1 BCX70KLT1

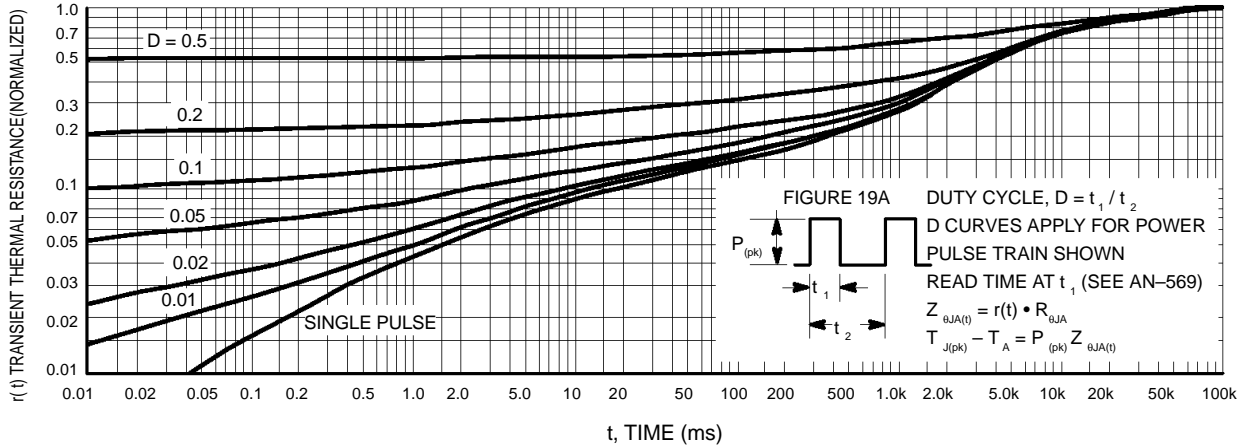


Figure 19. Thermal Response

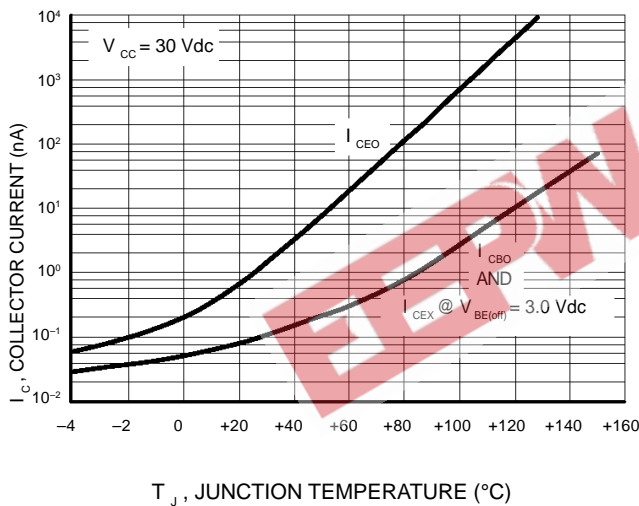


Figure 19A.

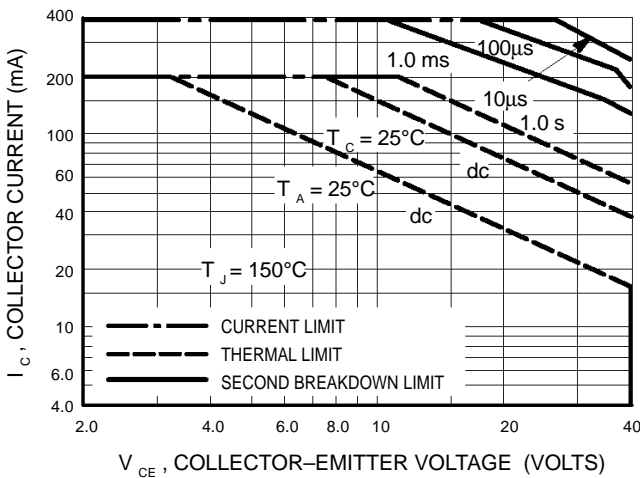


Figure 20.

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 19A. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 19 was calculated for various duty cycles.

To find  $Z_{\theta JA(t)}$ , multiply the value obtained from Figure 19 by the steady state value  $R_{\theta JA}$ .

Example:

The MPS3904 is dissipating 2.0 watts peak under the following conditions:

$t_1 = 1.0 \text{ ms}, t_2 = 5.0 \text{ ms. (D = 0.2)}$

Using Figure 19 at a pulse width of 1.0 ms and  $D = 0.2$ , the reading of  $r(t)$  is 0.22.

The peak rise in junction temperature is therefore

$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^\circ\text{C}.$

For more information, see AN-569.

The safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 20 is based upon  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  or  $T_A$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 19. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.